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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.256US0		10/052,924		
				Applicant(s)				Mokhlesi et al.
(Use several sheets if necessary)				Filing Date		Group		
JUL 09 2003				January 18, 2002		2818		
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HU	1	4,630,086	12/16/86	Sato et al.				
	2	5,172,338	12/15/92	Mehrotra et al.				
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	4	5,418,752	5/23/95	Harari et al.				
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		Document	Date	Country	Class	Subclass	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
HU	11	Bauza et al., "In-Depth Exploration of Si-SiO <sub>2</sub> Interface Traps in MOS Transistors Using the Charge Pumping Technique," <i>IEEE Transactions on Electron Devices</i> , Vol. 44, No. 12, December 1997, pp. 2262-2266.						
	12	Bloom, et al., "1/f Noise Reduction of Metal-Oxide-Semiconductor Transistors by Cycling from Inversion to Accumulation," <i>Appl. Phys. Lett.</i> 58 (15), 15 April 1991, pp. 1664-1666.						
	13	Dierickx et al., "The Decrease of "Random Telegraph Signal" Noise in Metal-Oxide-Semiconductor Field-Effect Transistors When Cycled from Inversion to Accumulation," <i>J. Appl. Phys.</i> 71 (4), 15 February 1992.						
	14	Hung et al., "Random Telegraph Noise of Deep-Submicrometer MOSFET's," <i>IEEE Electron Device Letters</i> , Vol. 11, No. 2, February 1990, pp. 90-92.						
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